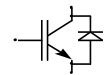


Technische Information / Technical Information

IGBT-Module
IGBT-Modules

BSM 200 GB 170 DLC

eupec



Höchstzulässige Werte / Maximum rated values

Elektrische Eigenschaften / Electrical properties

Kollektor-Emitter-Sperrspannung collector-emitter voltage		V_{CES}	1700	V
Kollektor-Dauergleichstrom DC-collector current	$T_C = 80^\circ\text{C}$	$I_{C,nom.}$	200	A
	$T_C = 25^\circ\text{C}$	I_C	400	A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	$t_p = 1\text{ ms}, T_C = 80^\circ\text{C}$	I_{CRM}	400	A
Gesamt-Verlustleistung total power dissipation	$T_C = 25^\circ\text{C}$, Transistor	P_{tot}	1660	W
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		V_{GES}	+/- 20V	V
Dauergleichstrom DC forward current		I_F	200	A
Periodischer Spitzenstrom repetitive peak forw. current	$t_p = 1\text{ ms}$	I_{FRM}	400	A
Grenzlastintegral der Diode I^2t - value, Diode	$V_R = 0\text{V}, t_p = 10\text{ms}, T_{vj} = 125^\circ\text{C}$	I^2t	11.000	A^2s
Isolations-Prüfspannung insulation test voltage	RMS, $f = 50\text{ Hz}, t = 1\text{ min.}$	V_{ISOL}	3,4	kV

Charakteristische Werte / Characteristic values

Transistor / Transistor

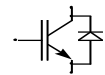
			min.	typ.	max.	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	$I_C = 200\text{A}, V_{GE} = 15\text{V}, T_{vj} = 25^\circ\text{C}$	$V_{CE\text{ sat}}$	-	2,6	3,2	V
	$I_C = 200\text{A}, V_{GE} = 15\text{V}, T_{vj} = 125^\circ\text{C}$		-	3,1	3,6	V
Gate-Schwellenspannung gate threshold voltage	$I_C = 9\text{mA}, V_{CE} = V_{GE}, T_{vj} = 25^\circ\text{C}$	$V_{GE(th)}$	4,5	5,5	6,5	V
Gateladung gate charge	$V_{GE} = -15\text{V} \dots +15\text{V}$	Q_G	-	2,4	-	μC
Eingangskapazität input capacitance	$f = 1\text{MHz}, T_{vj} = 25^\circ\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$	C_{ies}	-	15	-	nF
Rückwirkungskapazität reverse transfer capacitance	$f = 1\text{MHz}, T_{vj} = 25^\circ\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$	C_{res}	-	0,7	-	nF
Kollektor-Emitter Reststrom collector-emitter cut-off current	$V_{CE} = 1700\text{V}, V_{GE} = 0\text{V}, T_{vj} = 25^\circ\text{C}$	I_{CES}	-	0,05	0,5	mA
	$V_{CE} = 1700\text{V}, V_{GE} = 0\text{V}, T_{vj} = 125^\circ\text{C}$		-	6		mA
Gate-Emitter Reststrom gate-emitter leakage current	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}, T_{vj} = 25^\circ\text{C}$	I_{GES}	-	-	200	nA

prepared by: Regine Mallwitz

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revision: 2 (Series)



Charakteristische Werte / Characteristic values

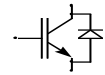
Transistor / Transistor

			min.	typ.	max.	
Einschaltverzögerungszeit (ind. Last) turn on delay time (inductive load)	$I_C = 200A, V_{CE} = 900V$	$t_{d,on}$	-	0,1	-	μs
	$V_{GE} = \pm 15V, R_G = 7,5\Omega, T_{vj} = 25^\circ C$		-	0,1	-	μs
Anstiegszeit (induktive Last) rise time (inductive load)	$I_C = 200A, V_{CE} = 900V$	t_r	-	0,1	-	μs
	$V_{GE} = \pm 15V, R_G = 7,5\Omega, T_{vj} = 125^\circ C$		-	0,1	-	μs
Abschaltverzögerungszeit (ind. Last) turn off delay time (inductive load)	$I_C = 200A, V_{CE} = 900V$	$t_{d,off}$	-	0,8	-	μs
	$V_{GE} = \pm 15V, R_G = 7,5\Omega, T_{vj} = 125^\circ C$		-	0,9	-	μs
Fallzeit (induktive Last) fall time (inductive load)	$I_C = 200A, V_{CE} = 900V$	t_f	-	0,03	-	μs
	$V_{GE} = \pm 15V, R_G = 7,5\Omega, T_{vj} = 125^\circ C$		-	0,03	-	μs
Einschaltverlustenergie pro Puls turn-on energy loss per pulse	$I_C = 200A, V_{CE} = 900V, V_{GE} = 15V$ $R_G = 7,5\Omega, T_{vj} = 125^\circ C, L_S = 60nH$	E_{on}	-	90	-	mWs
Abschaltverlustenergie pro Puls turn-off energy loss per pulse	$I_C = 200A, V_{CE} = 900V, V_{GE} = 15V$ $R_G = 7,5\Omega, T_{vj} = 125^\circ C, L_S = 60nH$	E_{off}	-	65	-	mWs
Kurzschlußverhalten SC Data	$t_F \leq 10\mu sec, V_{GE} \leq 15V, R_G = 7,5\Omega$ $T_{vj} \leq 125^\circ C, V_{CC} = 1000V, V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$	I_{SC}	-	800	-	A
Modulinduktivität stray inductance module		L_{SCE}	-	30	-	nH
Modulleitungswiderstand, Anschlüsse - Chip module lead resistance, terminals - chip	pro Zweig / per arm	R_{CC+EE}	-	0,6	-	m Ω

Charakteristische Werte / Characteristic values

Diode / Diode

			min.	typ.	max.	
Durchlaßspannung forward voltage	$I_F = 200A, V_{GE} = 0V, T_{vj} = 25^\circ C$	V_F	-	2,1	2,5	V
	$I_F = 200A, V_{GE} = 0V, T_{vj} = 125^\circ C$		-	2,1	2,5	V
Rückstromspitze peak reverse recovery current	$I_F = 200A, -di_F/dt = 2300A/\mu sec$	I_{RM}	-	160	-	A
	$V_R = 900V, V_{GE} = -10V, T_{vj} = 25^\circ C$ $V_R = 900V, V_{GE} = -10V, T_{vj} = 125^\circ C$		-	200	-	A
Sperrverzögerungsladung recovered charge	$I_F = 200A, -di_F/dt = 2300A/\mu sec$	Q_r	-	60	-	μAs
	$V_R = 900V, V_{GE} = -10V, T_{vj} = 25^\circ C$ $V_R = 900V, V_{GE} = -10V, T_{vj} = 125^\circ C$		-	105	-	μAs
Abschaltenergie pro Puls reverse recovery energy	$I_F = 200A, -di_F/dt = 2300A/\mu sec$	E_{rec}	-	25	-	mWs
	$V_R = 900V, V_{GE} = -10V, T_{vj} = 25^\circ C$ $V_R = 900V, V_{GE} = -10V, T_{vj} = 125^\circ C$		-	50	-	mWs



Thermische Eigenschaften / Thermal properties

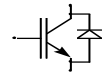
			min.	typ.	max.	
Innerer Wärmewiderstand thermal resistance, junction to case	Transistor / transistor, DC	R_{thJC}	-	-	0,075	K/W
	Diode/Diode, DC		-	-	0,15	K/W
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	pro Modul / per Module $d_{paste} \leq 50\mu m$ / $d_{grease} \leq 50\mu m$	R_{thCK}	-	-	0,012	K/W
Höchstzulässige Sperrschichttemperatur maximum junction temperature		T_{vj}	-	-	150	°C
Betriebstemperatur operation temperature		T_{op}	-40	-	125	°C
Lagertemperatur storage temperature		T_{stg}	-40	-	125	°C

Mechanische Eigenschaften / Mechanical properties

Gehäuse, siehe Anlage case, see appendix					
Innere Isolation internal insulation				Al_2O_3	
Kriechstrecke creepage distance				20	mm
Luftstrecke clearance				11	mm
CTI comperative tracking index					
Anzugsdrehmoment f. mech. Befestigung mounting torque		max.		5	Nm
Anzugsdrehmoment f. elektr. Anschlüsse terminal connection torque	terminals M6	max.		5	Nm
Gewicht weight		G		420	g

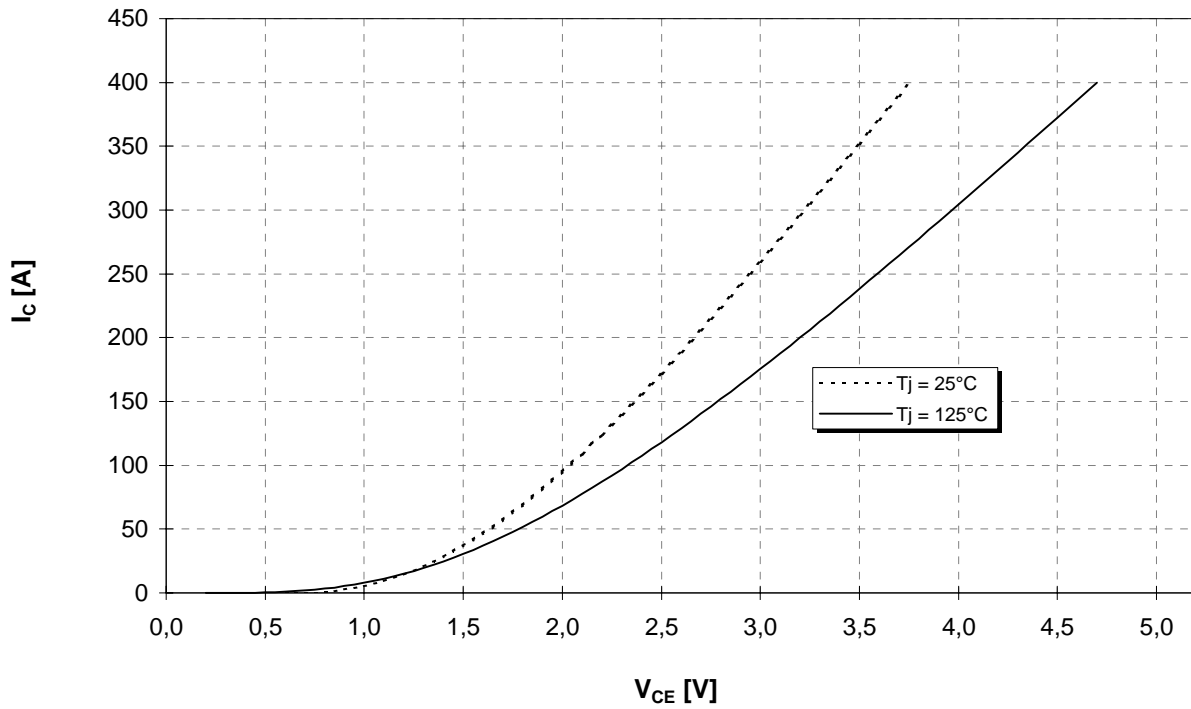
Mit dieser technischen Information werden Halbleiterbauelemente spezifiziert, jedoch keine Eigenschaften zugesichert. Sie gilt in Verbindung mit den zugehörigen Technischen Erläuterungen.

This technical information specifies semiconductor devices but promises no characteristics. It is valid in combination with the belonging technical notes.



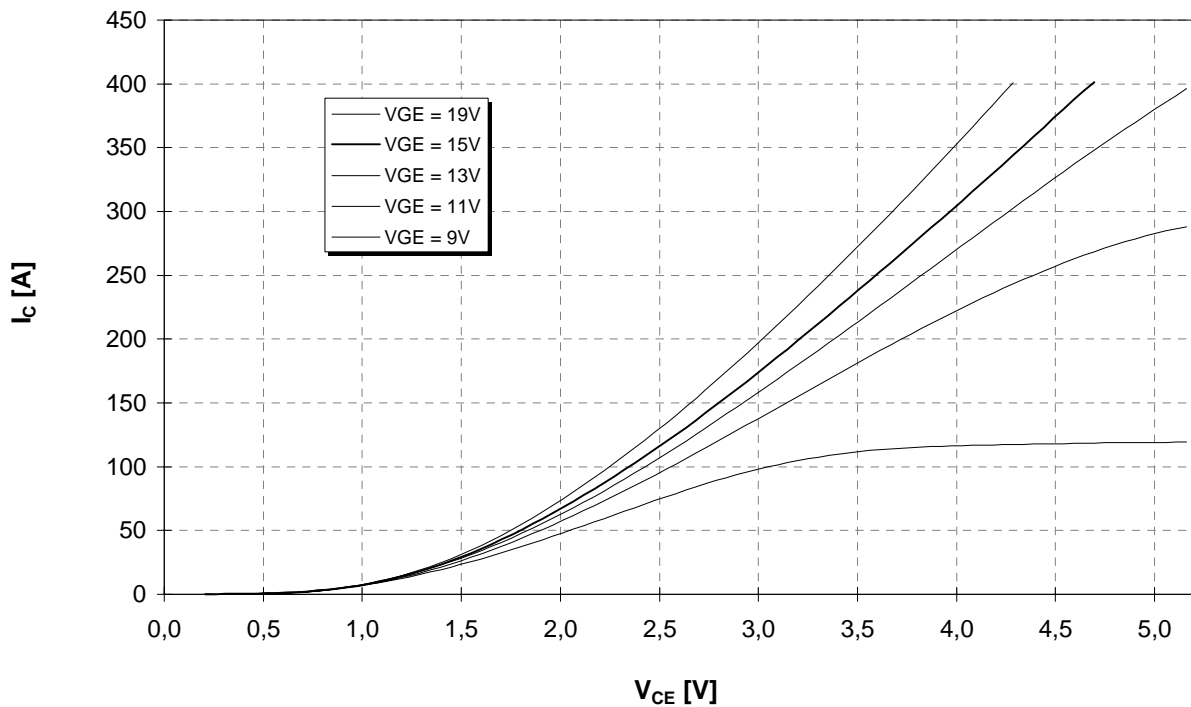
Ausgangskennlinie (typisch)
Output characteristic (typical)

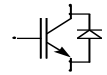
$I_C = f(V_{CE})$
 $V_{GE} = 15V$



Ausgangskennlinienfeld (typisch)
Output characteristic (typical)

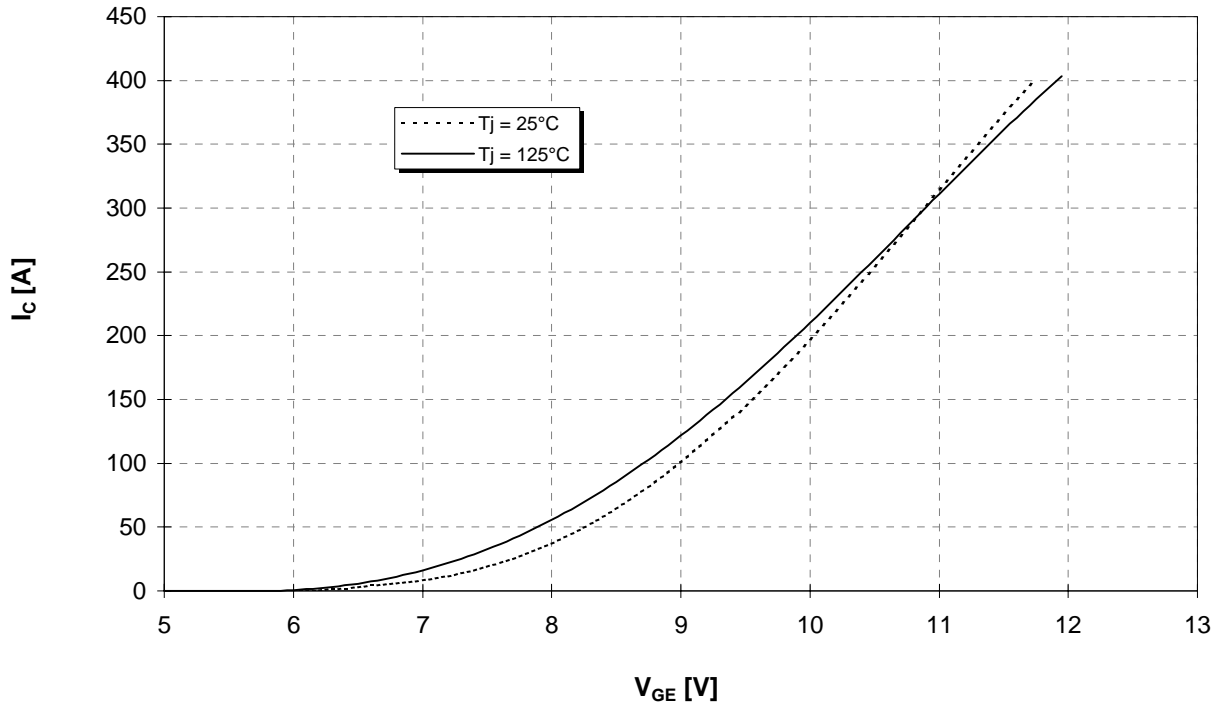
$I_C = f(V_{CE})$
 $T_{vj} = 125°C$





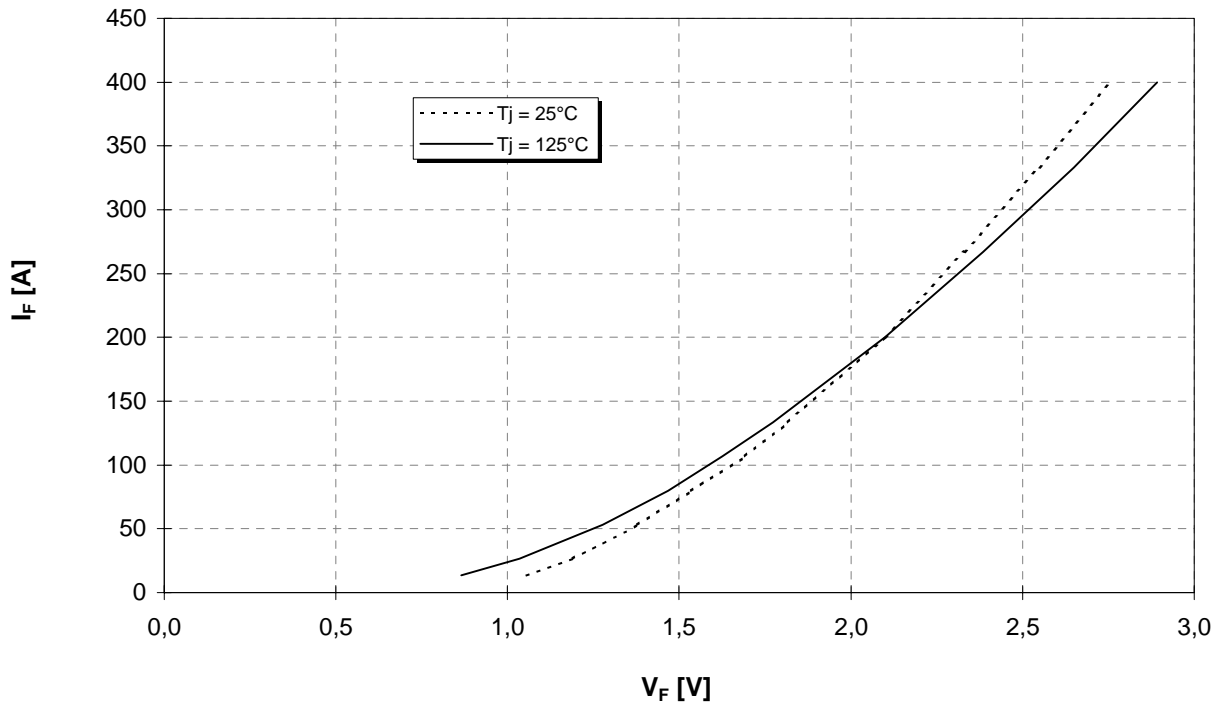
Übertragungscharakteristik (typisch)
Transfer characteristic (typical)

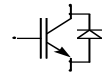
$I_C = f(V_{GE})$
 $V_{CE} = 20V$



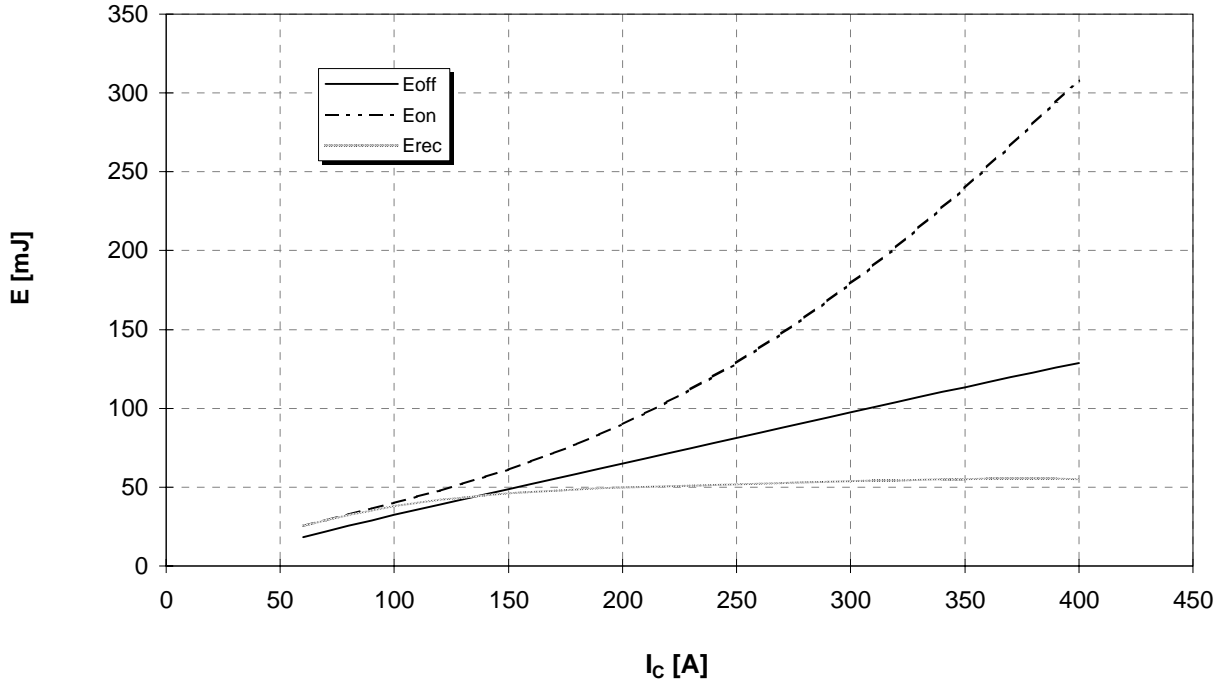
Durchlaßkennlinie der Inversdiode (typisch)
Forward characteristic of inverse diode (typical)

$I_F = f(V_F)$

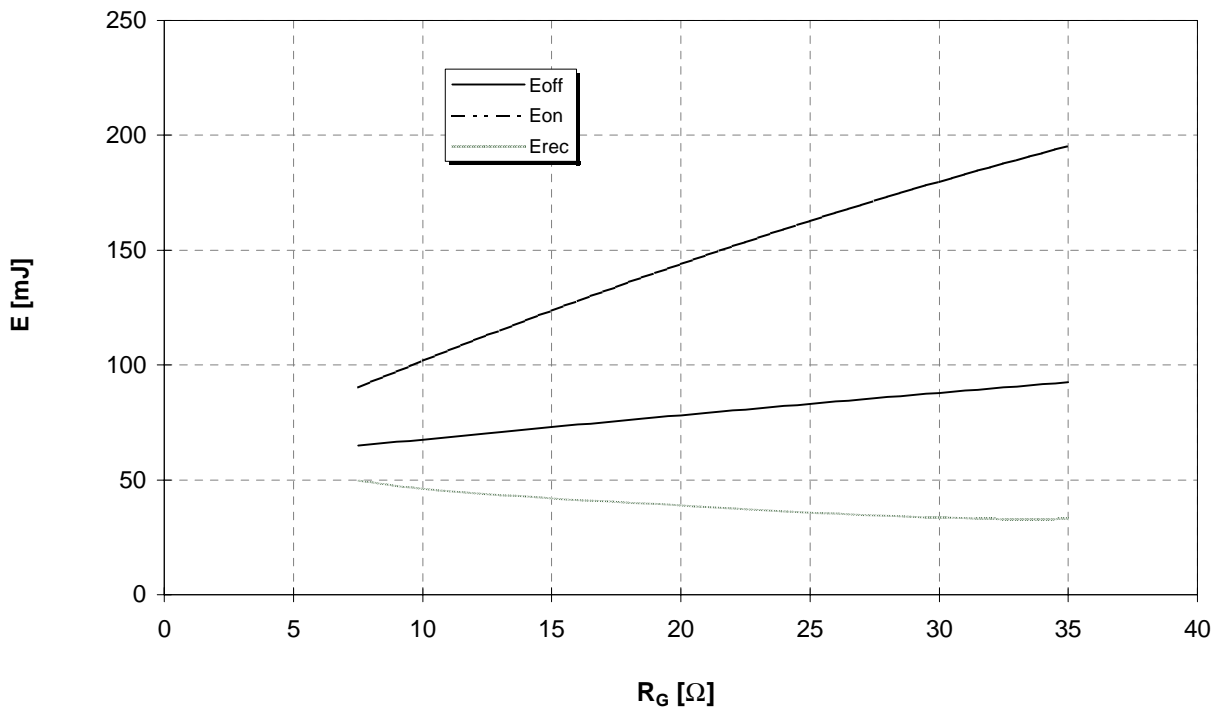


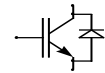


Schaltverluste (typisch) $E_{on} = f(I_C), E_{off} = f(I_C), E_{rec} = f(I_C)$
Switching losses (typical) $R_{gon} = R_{goff} = 7,5\Omega, V_{CE} = 900V, T_j = 125^\circ C$



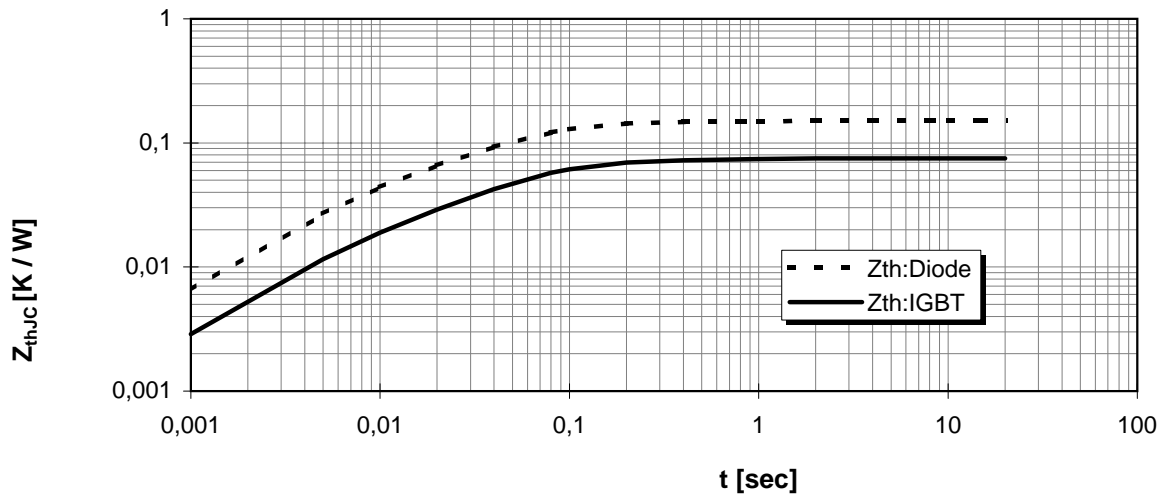
Schaltverluste (typisch) $E_{on} = f(R_G), E_{off} = f(R_G), E_{rec} = f(R_G)$
Switching losses (typical) $I_C = 200A, V_{CE} = 900V, T_j = 125^\circ C$





Transienter Wärmewiderstand
Transient thermal impedance

$Z_{thJC} = f(t)$



i		1	2	3	4
r_i [K/kW]	: IGBT	8,37	24,21	36,07	6,35
τ_i [sec]	: IGBT	0,0047	0,0356	0,0613	0,4669
r_i [K/kW]	: Diode	27,92	55,32	55,32	11,45
τ_i [sec]	: Diode	0,0062	0,0473	0,0473	0,2322

Sicherer Arbeitsbereich (RBSOA)

Reverse bias safe operation area (RBSOA)

$R_g = 7,5 \text{ Ohm}$, $T_{vj} = 125^\circ\text{C}$

